## MPS6717

## One Watt Amplifier <br> Transistor

## NPN Silicon

## Features

- $\mathrm{Pb}-$ Free Packages are Available*


## MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
| :---: | :---: | :---: | :---: |
| Collector-Emitter Voltage | $\mathrm{V}_{\text {CEO }}$ | 80 | Vdc |
| Collector-Base Voltage | $\mathrm{V}_{\text {CBO }}$ | 80 | Vdc |
| Emitter - Base Voltage | $\mathrm{V}_{\text {Ebo }}$ | 5.0 | Vdc |
| Collector Current - Continuous | $\mathrm{I}_{\mathrm{c}}$ | 500 | mAdc |
| Total Device Dissipation @ $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ Derate above $25^{\circ} \mathrm{C}$ | $\mathrm{P}_{\mathrm{D}}$ | $\begin{aligned} & 1.0 \\ & 8.0 \end{aligned}$ | $\underset{\mathrm{mW} /{ }^{\circ} \mathrm{C}}{\mathrm{~W}}$ |
| Total Device Dissipation @ $\mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}$ Derate above $25^{\circ} \mathrm{C}$ | $\mathrm{P}_{\mathrm{D}}$ | $\begin{aligned} & 2.5 \\ & 20 \end{aligned}$ | $\underset{\mathrm{mW} /{ }^{\circ} \mathrm{C}}{\mathrm{~W}}$ |
| Operating and Storage Junction Temperature Range | $\mathrm{T}_{\mathrm{J}}, \mathrm{T}_{\text {stg }}$ | -55 to +150 | ${ }^{\circ} \mathrm{C}$ |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
| :---: | :---: | :---: | :---: |
| Thermal Resistance, Junction-to-Ambient | $\mathrm{R}_{\theta J A}$ | 125 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Thermal Resistance, Junction-to-Case | $\mathrm{R}_{\theta \mathrm{JC}}$ | 50 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor ${ }^{\circledR}$
http://onsemi.com


MARKING DIAGRAM


MPS6717 = Device Code
A = Assembly Location
Y = Year
WW = Work Week

- = Pb-Free Package
(Note: Microdot may be in either location)


## ORDERING INFORMATION

| Device | Package | Shipping $^{\dagger}$ |
| :--- | :---: | :---: |
| MPS6717 | TO-92 | 5000 Units / Bulk |
| MPS6717G | TO-92 <br> (Pb-Free) | 5000 Units / Bulk |
| MPS6717RLRA | TO-92 | 2000/Tape \& Reel |
| MPS6717RLRAG | TO-92 <br> (Pb-Free) | 2000/Tape \& Reel |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS $\left(\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}\right.$ unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: |
| OFF CHARACTERISTICS |  |  |  |  |
| Collector-Emitter Breakdown Voltage (Note 1) $\left(\mathrm{I}_{\mathrm{C}}=1.0 \mathrm{mAdc}, \mathrm{I}_{\mathrm{B}}=0\right)$ | $\mathrm{V}_{\text {(BR)CEO }}$ | 80 | - | Vdc |
| Collector-Base Breakdown Voltage $\left(I_{C}=100 \mu A d c, I_{E}=0\right)$ | $\mathrm{V}_{\text {(BR) }} \mathrm{CBO}$ | 80 | - | Vdc |
| Emitter-Base Breakdown Voltage $\left(\mathrm{I}_{\mathrm{E}}=10 \mu \mathrm{Adc}, \mathrm{I}_{\mathrm{C}}=0\right)$ | $\mathrm{V}_{\text {(BR) }{ }^{\text {EBO }}}$ | 5.0 | - | Vdc |
| Collector Cutoff Current $\left(\mathrm{V}_{\mathrm{CB}}=60 \mathrm{Vdc}, \mathrm{I}_{\mathrm{E}}=0\right)$ | $\mathrm{I}_{\text {CBO }}$ | - | 0.1 | $\mu \mathrm{Adc}$ |
| Emitter Cutoff Current $\left(\mathrm{V}_{\mathrm{EB}}=5.0 \mathrm{Vdc}, \mathrm{I}_{\mathrm{C}}=0\right)$ | $\mathrm{I}_{\text {ebo }}$ | - | 10 | $\mu \mathrm{Adc}$ |

ON CHARACTERISTICS

| DC Current Gain <br> $\left(I_{C}=50 \mathrm{mAdc}, \mathrm{V}_{\mathrm{CE}}=1.0 \mathrm{Vdc}\right)$ <br> $\left(\mathrm{I}_{\mathrm{C}}=250 \mathrm{mAdc}, \mathrm{V}_{\mathrm{CE}}=1.0 \mathrm{Vdc}\right)$ | $\mathrm{h}_{\mathrm{FE}}$ |  |  | - |
| :---: | :---: | :---: | :---: | :---: |
| Collector-Emitter Saturation Voltage <br> $\left(\mathrm{I}_{\mathrm{C}}=250 \mathrm{mAdc}, \mathrm{I}_{\mathrm{B}}=10 \mathrm{mAdc}\right)$ |  | $\mathrm{V}_{\mathrm{CE}(\mathrm{sat})}$ | - | 0.5 |
| Base-Emitter On Voltage <br> $\left(\mathrm{I}_{\mathrm{C}}=250 \mathrm{mAdc}, \mathrm{V}_{\mathrm{CE}}=1.0 \mathrm{Vdc}\right)$ | $\mathrm{V}_{\mathrm{BE}(\mathrm{on})}$ | - | 1.2 | Vdc |

SMALL-SIGNAL CHARACTERISTICS

| Collector-Base Capacitance <br> $\left(\mathrm{V}_{\mathrm{CB}}=10 \mathrm{Vdc}, \mathrm{I}_{\mathrm{E}}=0, \mathrm{f}=1.0 \mathrm{MHz}\right)$ | $\mathrm{C}_{\mathrm{cb}}$ | - | 30 | pF |
| :---: | :---: | :---: | :---: | :---: |
| Small-Signal Current Gain <br> $\left(\mathrm{I}_{\mathrm{C}}=200 \mathrm{mAdc}, \mathrm{V}_{\mathrm{CE}}=5.0 \mathrm{Vdc}, \mathrm{f}=20 \mathrm{MHz}\right)$ | $\mathrm{h}_{\mathrm{fe}}$ | 2.5 | 25 | - |

1. Pulse Test: Pulse Width $\leq 300 \mu \mathrm{~s}$; Duty Cycle $\leq 2.0 \%$.


Figure 1. DC Current Gain


Figure 2. Collector Saturation Region


Figure 4. Base-Emitter Temperature Coefficient


Figure 6. Current-Gain - Bandwidth Product


Figure 3. "On" Voltages


Figure 5. Capacitance


Figure 7. Active Region - Safe Operating Area


STRAIGHT LEAD


BENT LEAD

TO-92 (TO-226) 1 WATT
CASE 29-10
ISSUE B
DATE 12 NOV 2020


TOP VIEW

NDTES:

1. DIMENSIDNING AND TZLERANCING PER ASME Y14.5M, 2009.
2. CDNTRZLLING DIMENSIDN: MILLIMETERS
3. DIMENSIDNS D AND E DD NDT INCLUDE MDLD FLASH DR GATE PRDTRUSIDNS.
4. DIMENSIDN b AND b己 DDES NDT INCLUDE DAMBAR PRDTRUSIDN. LEAD WIDTH INCLUDING PRZTRUSIDN SHALL NDT EXCEED 0.20.

| DIM | MILLIMETERS |  |  |
| :--- | :---: | :---: | :---: |
|  | MIN. | NDM. | MAX. |
| A | 3.75 | 3.90 | 4.05 |
| A1 | 1.28 | 1.43 | 1.58 |
| b | 0.38 | 0.465 | 0.55 |
| b2 | 0.62 | 0.70 | 0.78 |
| c | 0.35 | 0.40 | 0.45 |
| D | 7.85 | 8.00 | 8.15 |
| E | 4.75 | 4.90 | 5.05 |
| E2 | 3.90 | 4.00 | 4.10 |
| e | 1.27 BSC |  |  |
| L | 13.80 | 14.00 | 14.20 |

STYLES AND MARKING ON PAGE 3

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CASE 29-10
ISSUE B
DATE 12 NOV 2020

FIRMED LEAD


NDTES:

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2. CDNTRZLLING DIMENSIDN: MILLIMETERS
3. DIMENSIDNS D AND E DU NUT INCLUDE MDLD FLASH GR GATE PRDTRUSIDNS.
4. DIMENSIDN b AND b2 DOES NDT INCLUDE DAMBAR PRDTRUSIDN. LEAD WIDTH INCLUDING PRDTRUSIDN SHALL NDT EXCEED 0.20.

| DIM | MILLIMETERS |  |  |
| :--- | :---: | :---: | :---: |
|  | MIN. | NDM. | MAX. |
| A | 3.75 | 3.90 | 4.05 |
| A1 | 1.28 | 1.43 | 1.58 |
| b | 0.38 | 0.465 | 0.55 |
| b2 | 0.62 | 0.70 | 0.78 |
| C | 0.35 | 0.40 | 0.45 |
| D | 7.85 | 8.00 | 8.15 |
| E | 4.75 | 4.90 | 5.05 |
| E2 | 3.90 | 4.00 | 4.10 |
| e | 2.50 BSC |  |  |
| L | 13.80 | 14.00 | 14.20 |
| L2 | 13.20 | 13.60 | 14.00 |
| L3 | 3.00 REF |  |  |

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## TO-92 (TO-226) 1 WATT

CASE 29-10
ISSUE B

| STYLE 1: |  |
| :---: | :---: |
| PIN 1. | EMITTER |
| 2. | BASE |
| 3. | COLLECTOR |
| STYLE 6: |  |
| PIN 1. | GATE |
| 2. | SOURCE \& SUBSTRATE |
| 3. | DRAIN |
| STYLE 11: |  |
| PIN 1. | ANODE |
| 2. | CATHODE \& ANODE |
| 3. | CATHODE |
| STYLE 16: |  |
| PIN 1. | ANODE |
| 2. | GATE |
| 3. | CATHODE |
| STYLE 21: |  |
| PIN 1. | COLLECTOR |
| 2. | Emitter |
| 3. | BASE |
| STYLE 26: |  |
| PIN 1. | $\mathrm{V}_{\mathrm{cc}}$ |
| 2. | GROUND 2 |
| 3. | OUTPUT |
| STYLE 31: |  |
| PIN 1. | GATE |
| 2. | DRAIN |
| 3. | SOURCE |


| STYLE 2: |  |
| :--- | :--- |
| PIN 1. | BASE |
| 2. | EMITTER |
| 3. | COLLECTOR |
| STYLE 7: |  |
| PIN 1. | SOURCE |
| 2. | DRAIN |
| 3. | GATE |
| STYLE 12: |  |
| PIN 1. MAIN TERMINAL 1 |  |
| 2. | GATE |
| 3. | MAIN TERMINAL 2 |
| STYLE 17: |  |
| PIN 1. | COLLLECTOR |
| 2. | BASE |
| 3. | EMITTER |
| STYLE 22: |  |
| PIN 1. | SOURCE |
| 2. | GATE |
| 3. | DRAIN |
| STYLE 27: |  |
| PIN 1. MT |  |
| 2. | SUBSTRATE |
| 3. | MT |
| STYLE 32: |  |
| PIN 1. | BASE |
| 2. | COLLECTOR |
| 3. |  |


| STYLE 3: |  |
| :---: | :---: |
| PIN 1. | ANODE |
| 2. | ANODE |
| 3. | CATHODE |
| STYLE 8: |  |
| PIN 1. | DRAIN |
| 2. | GATE |
| 3. | SOURCE \& SUBSTRATE |
| STYLE 13: |  |
| PIN 1. | ANODE 1 |
| 2. | GATE |
| 3. | CATHODE 2 |
| STYLE 18: |  |
| PIN 1. | ANODE |
| 2. | CATHODE |
| 3. | NOT CONNECTED |
| STYLE 23: |  |
| PIN 1. | GATE |
| 2. | SOURCE |
| 3. | DRAIN |
| STYLE 28: |  |
| PIN 1. | CATHODE |
| 2. | ANODE |
| 3. | GATE |
| STYLE 33: |  |
| PIN 1. | RETURN |
| 2. | INPUT |
| 3. | OUTPUT |


| STYLE 4: |  | STYLE 5: |  |
| :---: | :---: | :---: | :---: |
| PIN 1. | CATHODE | PIN 1. | DRAIN |
| 2. | CATHODE | 2. | SOURCE |
| 3. | ANODE | 3. | GATE |
| STYLE 9: |  | STYLE 10: |  |
| PIN 1. | BASE 1 | PIN 1. | CATHODE |
| 2. | EMITTER | 2. |  |
| 3. | BASE 2 | 3. | ANODE |
| STYLE 14 |  | STYLE 15: |  |
| PIN 1. | EMITTER | PIN 1. | ANODE 1 |
| 2. | COLLECTOR | 2. | CATHODE |
| 3. | BASE | 3. | ANODE 2 |
| STYLE 19: |  | STYLE 20: |  |
| PIN 1. | GATE | PIN 1. | NOT CONNECTED |
| 2. | ANODE | 2. | CATHODE |
| 3. | CATHODE | 3. | ANODE |
| STYLE 24 |  | STYLE 25: |  |
| PIN 1. | EMITTER | PIN 1. | MT 1 |
| 2. | COLLECTOR/ANODE | 2. | GATE |
| 3. | CATHODE | 3. | MT 2 |
| STYLE 29: |  | STYLE 30: |  |
| PIN 1. | NOT CONNECTED | PIN 1. | DRAIN |
| 2. | ANODE | 2. | GATE |
| 3. | CATHODE | 3. | SOURCE |
| STYLE 34 |  | STYLE 35: |  |
| PIN 1. | INPUT | PIN 1. | GATE |
| 2. | GROUND | 2. | COLLECTOR |
| 3. | LOGIC | 3. | Emitter |

GENERIC
MARKING DIAGRAM*
XXXXX
XXXXX
ALYW•
$\quad$.

XXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week

- = Pb-Free Package
(Note: Microdot may be in either location)
*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-$ Free indicator, " G " or microdot " $\mathrm{\square}$ ", may or may not be present. Some products may not follow the Generic Marking.

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